

## GE2026

### NPN EPITAXIAL PLANAR TRANSISTOR

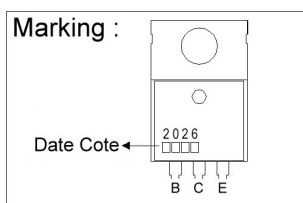
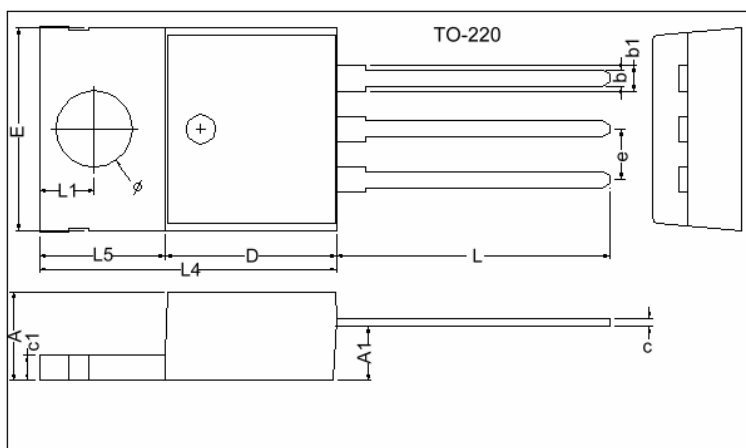
#### Description

The GE2026 is designed for general purpose application.

#### Features

- Low Collector Saturation Voltage :  $V_{CE(sat)} = 1.0V$  (Max.) @  $I_C=2A, I_B=0.2A$ ,

#### Package Dimensions



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	4.40	4.80	c1	1.25	1.45
b	0.76	1.00	b1	1.17	1.47
c	0.36	0.50	L	13.25	14.25
D	8.60	9.00	e	2.54 REF.	
E	9.80	10.4	L1	2.60	2.89
L4	14.7	15.3	∅	3.71	3.96
L5	6.20	6.60	A1	2.60	2.80

#### Absolute Maximum Ratings ( $T_A=25^\circ C$ )

Parameter		Symbol	Ratings	Unit
Collector to Base Voltage		$V_{CBO}$	60	V
Collector to Emitter Voltage		$V_{CEO}$	60	V
Emitter to Base Voltage		$V_{EBO}$	7	V
Collector Current		$I_C$	3	A
Base Current		$I_B$	0.5	A
Total Device Dissipation	$T_A=25^\circ C$	$P_D$	2	W
	$T_C=25^\circ C$	$P_D$	20	W
Junction Temperature		$T_J$	150	$^\circ C$
Storage Temperature		$T_{stg}$	-55 ~ +150	$^\circ C$

#### Electrical Characteristics ( $T_A = 25^\circ C$ unless otherwise noted)

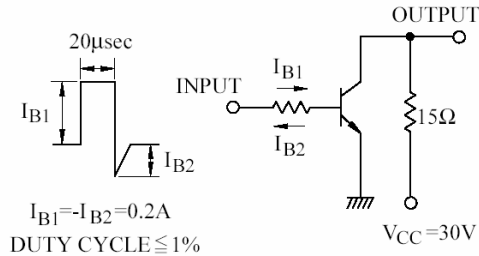
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
$V_{CBO}$	60	-	-	V	$I_C=100\mu A, I_E=0$
$V_{CEO}$	60	-	-	V	$I_C=50mA, I_B=0$
$V_{EBO}$	7	-	-	V	$I_E=100\mu A, I_C=0$
$I_{CBO}$	-	-	100	$\mu A$	$V_{CB}=60V, I_E=0$
$I_{EBO}$	-	-	100	$\mu A$	$V_{EB}=7V, I_C=0$
* $V_{CE(sat)}$	-	-	1.0	V	$I_C=2A, I_B=0.2A$
* $V_{BE(on)}$	-	-	1.0	V	$V_{CE}=5V, I_C=0.5A$
* $h_{FE1}$	100	-	320		$V_{CE}=5V, I_C=0.5A$
* $h_{FE2}$	20	-	-		$V_{CE}=5V, I_C=3A$
fT	-	30	-	MHz	$V_{CE}=5V, I_C=0.5A$
Cob	-	35	-	pF	$V_{CB}=10V, I_E=0, f=1MHz$
ton (Turn-on Time)	-	0.65	-	uS	See specified test circuit
tstg (Storage Time)	-	1.3	-		
tf (Fall Time)	-	0.65	-		

\*Pulse Test: Pulse Width  $\leq 380\mu s$ , Duty Cycle  $\leq 2\%$

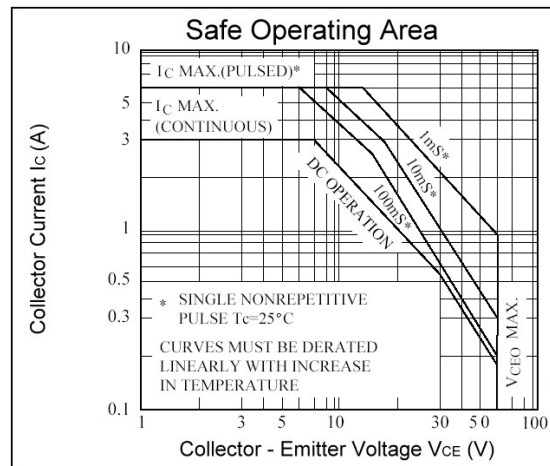
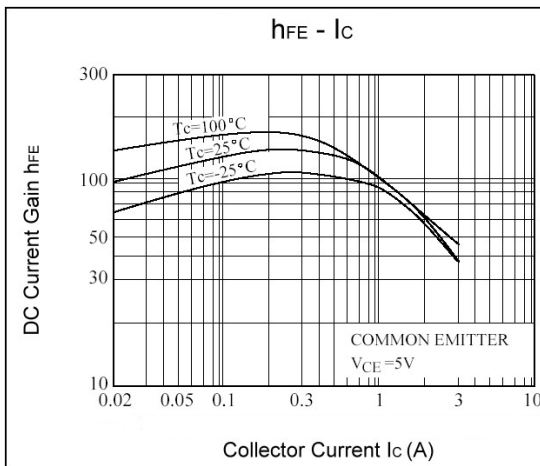
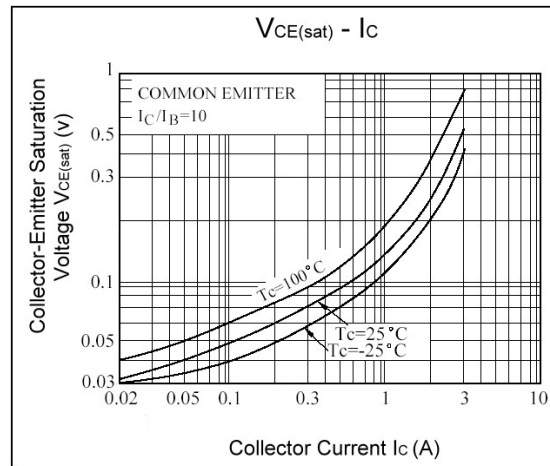
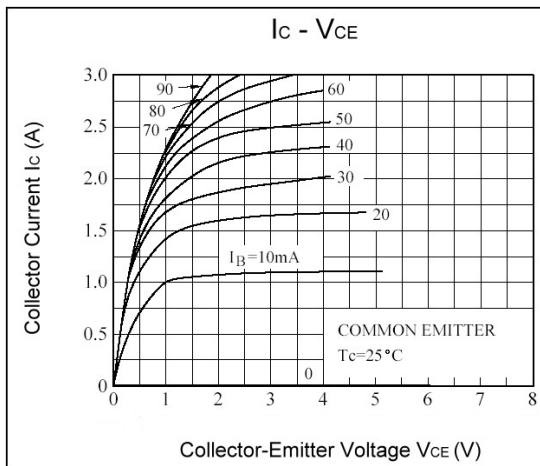
## Classification Of hFE1

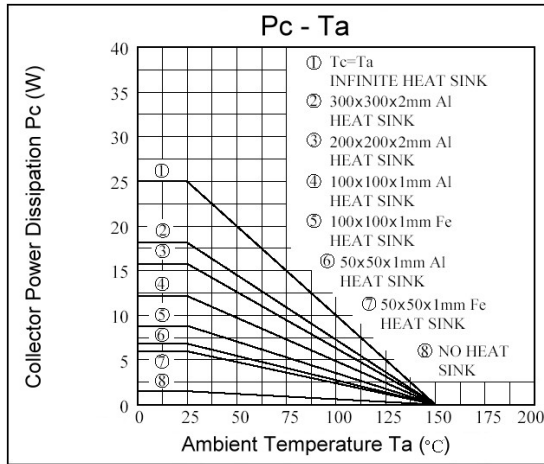
Rank	Y	GR
Range	100 - 200	160 - 320

## Switching Time Test Circuit



## Characteristics Curve





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**Head Office And Factory:**

- **Taiwan:** No. 17-1 Tatung Rd. Fu Kou Hsin-Chu Industrial Park, Hsin-Chu, Taiwan, R. O. C.
- TEL : 886-3-597-7061 FAX : 886-3-597-9220, 597-0785
- **China:** (201203) No.255, Jang-Jiang Tsai-Lueng RD. , Pu-Dung-Hsin District, Shang-Hai City, China
- TEL : 86-21-5895-7671 ~ 4 FAX : 86-21-38950165